

TOSHIBA Diode Silicon Epitaxial Planar Type

JDV2S14E

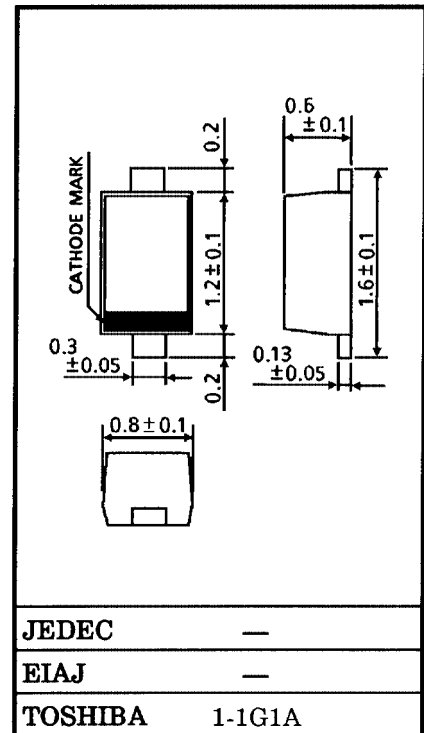
Useful for VCO/TCXO

- Small Package
- High Capacitance Ratio: $C_{1V}/C_{2.5V} = 2.15$ (typ.)
- Low Series Resistance : $r_s = 0.4 \Omega$ (typ.)

Maximum Ratings (Ta = 25°C)

Characteristics	Symbol	Rating	Unit
Reverse voltage	V_R	10	V
Junction temperature	T_j	125	°C
Storage temperature range	T_{stg}	-55~125	°C

Unit in mm



Weight: 0.0014 g

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Electrical Characteristics (Ta = 25°C)

Characteristics	Symbol	Test Condition	Min	Typ.	Max	Unit
Reverse voltage	V_R	$I_R = 1\ \mu\text{A}$	10	—	—	V
Reverse current	I_R	$V_R = 10\ \text{V}$	—	—	3	nA
Capacitance	$C_{0.5\text{V}}$	$V_R = 0.5\ \text{V}, f = 1\ \text{MHz}$	56.3	—	64.7	pF
	$C_{1\text{V}}$	$V_R = 1\ \text{V}, f = 1\ \text{MHz}$	44	—	49.5	
	$C_{2.5\text{V}}$	$V_R = 2.5\ \text{V}, f = 1\ \text{MHz}$	19	—	26.5	
	$C_{4\text{V}}$	$V_R = 4\ \text{V}, f = 1\ \text{MHz}$	9.2	—	12	
Capacitance ratio	$C_{0.5\text{V}}/C_{1\text{V}}$	—	1.25	—	1.35	—
	$C_{1\text{V}}/C_{2.5\text{V}}$	—	1.99	2.15	2.3	
Series resistance	r_s	$V_R = 4\ \text{V}, f = 100\ \text{MHz}$	—	0.4	0.8	Ω

Note: Signal level when capacitance is measured. $V_{\text{sig}} = 500\ \text{mV}_{\text{rms}}$

Marking



